

# M52045FP

# PAL Video Chroma Signal Processor

REJ03F0181-0200 Rev.2.00 Sep 14, 2006

## **Description**

The M52045FP is a semiconductor integrated circuit for video signal processing that been developed for PAL system liquid crystal (LCD) color TV. This IC has a built-in luminance signal processing circuit and color signal processing circuit, which is employed to convert a composite video signal to an RGB signal.

#### **Features**

- Low voltage and low power dissipation design
- Built-in Y/C separation circuit and external chroma trap switchable (fc is nearly equal to 1.5 MHz)
- Built-in sync separation circuit
- Provided with Y-signal blanking function by HD pulse
- R.G.B. signal output
- Tint, contrast, picture quality and color control linearly adjustable
- 24-pin, shrink pitch, flat package employed
- Same package as in NTSC system video chroma IC M52042FP, pins perfectly compatible

## **Application**

LCD color TV and LCD color view finder

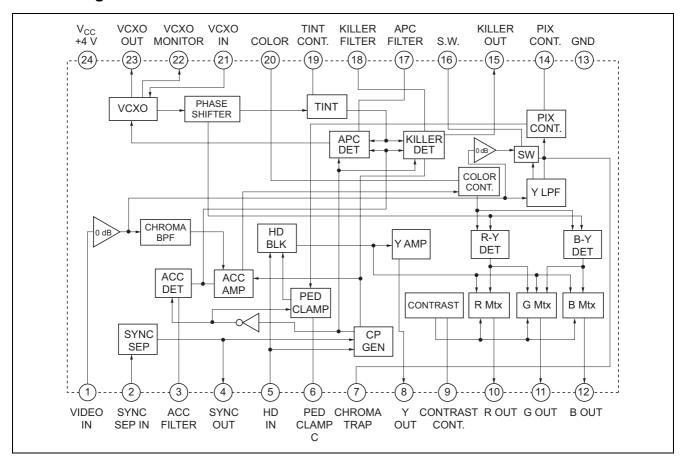
## **Recommended Operating Condition**

Supply voltage range: 3.8 to 4.2 V

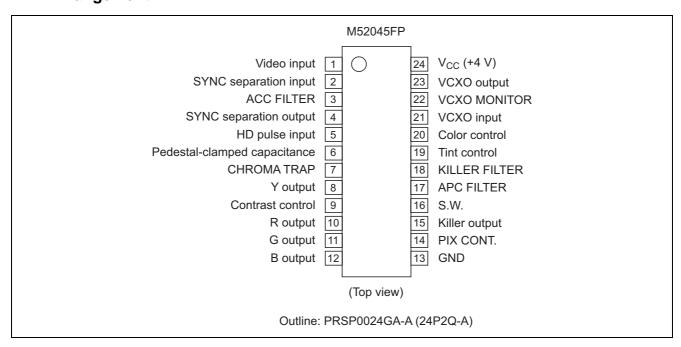
Rated supply voltage: 4.0 V



## **Block Diagram**



## **Pin Arrangement**



## **Pin Description**

Pin No.	Name	Peripheral Circuit of Pins
1	VIDEO IN (Video input)	The state of the s
2	SYNC SEP IN (SYNC separation input)	Bias GND
3	ACC FILTER	W 47 k GND 3
4	SYNC OUT (SYNC separation output)	V <sub>CC</sub> 100 k ≥ ≥10 k  GND
5	HD IN (HD pulse input)	50 k 100 k 300 k 3

Pin No.	Name	Peripheral Circuit of Pins
6	PED CLAMP C	(6)
	(Pedestal-clamped capacitance)	V <sub>CC</sub>
		Bias \$5 k GND
7	CHROMA TRAP	(7)
		V <sub>CC</sub>
8	Y OUT (Y output)	V <sub>CC</sub> \$ \$150 k \$40 k  8  10 k  GND
9	CONTRAST CONT. (Contrast control)	5 k \$ 5 k 9 9 \$ 30 k GND
10	R OUT (R output)	V <sub>CC</sub>
11	G OUT (G output)	
12	B OUT (B output)	Bias \$360 GND
13	GND (Grounding)	_
24	V <sub>CC</sub> +4 V (Power supply)	_

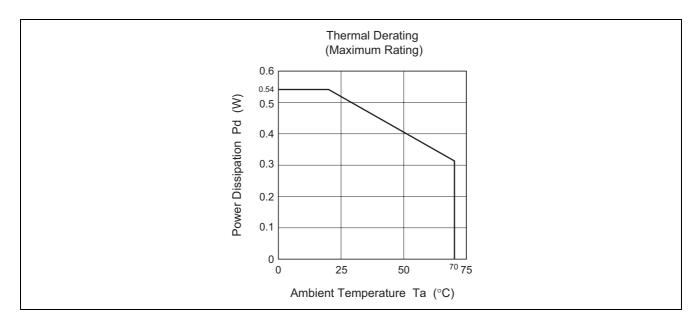
Pin No.	Name	Peripheral Circuit of Pins
16	S.W.	(16) V <sub>CC</sub>
	(Selector switch)	Y T
		χ κ γ 10 k ₹
		10 k
		10 k
		' '
		₹ * }
		GND
22	VCXO MONITOR	V
		VCC T
		7
		* The state of the
		10 k
		\$\\$\\$\\$\\$\\$
		GND
14	PIX CONT. (Picture quality control)	V <sub>cc</sub> (14)
	(i icture quality control)	₹ \$100 k
		36 k≶ 36 k≶ 100 k
15	KILLER OUT	→ Vcc
	(Killer output)	100 k≩
		(15)
		100 k≩
47	ADO SU TED	
17	APC FILTER	V <sub>C</sub> C
		*
		10 k
		10 k
		(T) GND
		<u> </u>

Pin No.	Name	Peripheral Circuit of Pins
18	KILLER FILTER	
		41 k %──₩
		18 <u>GND</u>
19	TINT CONT. (Tint control)	V <sub>CC</sub>
	(Till Control)	* *
		15 k 2 k4
		15 k
		∫ **** 160 k≩
		Bias
		\$ (19) → GND
20	COLOR	V <sub>CC</sub>
	(Color control)	
		▼
		20
21	VCXO IN	<b>2</b> 1
	(VCXO input)	Vcc
		30 k
		22 k
		Bias
		\$2 k
23	VCXO OUT	GND
23	(VCXO output)	V <sub>CC</sub> — ₹ 500
		> 5000
		1 k 15 k ≨
		23
		Bias —
		<b>\$</b> 180
		——— GND

## **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit
Supply voltage	V <sub>CC</sub>	4.5	V
Power dissipation	Pd	680	mW
Operating temperature	Topr	-10 to 70	°C
Storage temperature	Tstg	-45 to 120	°C
Thermal derating	Кө	5.4	mW/°C
Electrostatic capacity	Vmax	±200*	V

Note: Charging capacitance: 200 pF



## **Electrical Characteristics**

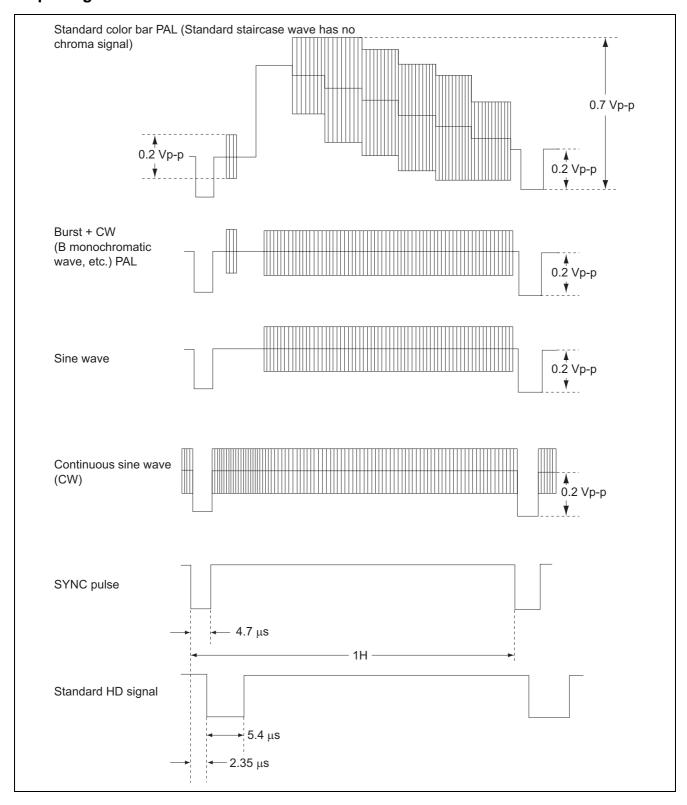
(Ta = 25°C, unless otherwise noted)

Item	Symbol	Min	Тур	Max	Unit	Test No.	Test Conditions
Circuit current	I <sub>CC</sub>		1 <b>yp</b>	21	mA	1	Input standard color bar signal of $V_{CC} = 4 \text{ V}$ .
SYNC SEP section		''		1117 (		impar standard obior bar digital of V(C = 1 V.	
SYNC tip voltage	Vsync 1	2.20	2.30	2.40	V	2	Measure each output signal SYNC tip
	Vsync 7	1.25	1.40	1.50			voltage at pins (1), (7) when standard color bar signal of 0.7 Vp-p is input.
SYNC output	Vsync H	2.7	3.1	3.4	Vp-p	3	Input only SYNC pulse of pulse width 4.7μs
amplitude	Vsync L	2.7	3.1	3.4			to pin (1). Measure the output amplitude at pin (4) when the input SYNC pulse amplitudes are 0.2 and 0.05 Vp-p.
SYNC output	Tsync H	3.7	4.7	5.7	μS	4	Input only SYNC pulse of pulse width 4.7µs
pulse width	Tsync L	3.7	4.7	5.7			to pin (1). Measure the output amplitude at pin (4) when the input SYNC pulse amplitudes are 0.2 and 0.05 Vp-p.
SYNC output	Dsync H	3.7	4.7	6.0	μS	5	Input only SYNC pulse of pulse width 4.7μs
pulse delay	Dsync L	3.7	4.7	6.0			to pin (1). Measure the pulse width + delay time when the input SYNC pulse amplitudes are 0.2 and 0.05 Vp-p.
Video section							
YLPF frequency	VLPF (L)	1.45	1.55	_	MHz	6	Measure the frequency at which the sine
characteristics	VLPF (H)	-30	-24	-21	dB		wave output amplitude is -3 dB when the
(Pin (7))							input signal (∭∭∭∏ Ţ 0.2 Vp-p ) 0.2 Vp-p
							is input. Also measure the output gain at input sine wave 3.58 MHz.
Maximum output	Ymax	1.1	1.4	1.7	Vp-p	7	Input standard staircase wave of 0.7 Vp-p.  Measure the output amplitude at pin (12) when V9 is 0 V.
Video amplifier gain	Gymax	4.0	6.0	8.0	dB	8	Input standard staircase wave of 0.7 Vp-p. Calculate the ratio between the output amplitude at pin (12) and input amplitude when V9 is 1.7 V.
Contrast control	Yctrast (1)	1.20	2.45	4.50	dB	9	Input standard staircase wave of 0.7 Vp-p,
characteristics	Yctrast (2, 5)	-7.3	-5.0	-2.7			and calculate the ratio of the input amplitude
	Yctrast (3, 5)	_	-30	-17			to the output amplitude in Test No.8 above when V9 is changed to 1 V, 2.5 V and 3.5 V.
PIX control	XPIX (4)	-3.5	-2.0	-0.5	dB	10	Input 1.5 MHz sine wave of 0.2 Vp-p to the
characteristics	XPIX (0)	10.0	12.0	14.0	dB		input. Measure the output amplitude at pin (12) when V9 is 1.7 V, and V14 is charged to 2, 4 and 0 V and calculate the ratio between the input resectively and the output amplitude when V14 = 2 V.
Y AMP gain	Gymap	9.1	11.0	12.6	dB	11	Input standard staircase wave of 0.7 Vp-p and calculate the ratio between the output amplitudes at pin (8) and input amplitude.
PED offset level	Vped	0.00	0.05	0.06	_	12	When input SYNC pulse at 0.2 Vp-p, measure pin (12) output pedestal offset and calculate ratio of the offset to that when 0.7 Vp-p standard staircase is input.

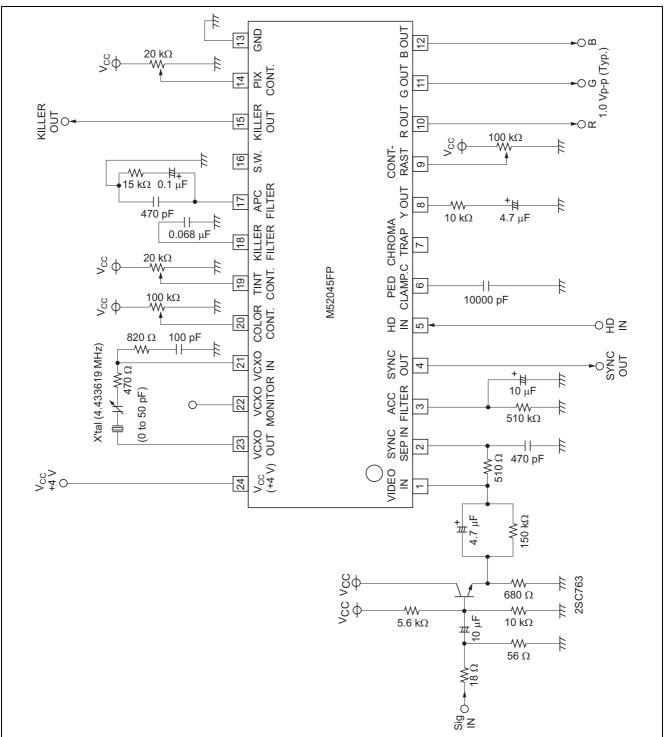
# **Electrical Characteristics (cont.)**

				1		Test	_
Item	Symbol	Min	Тур	Max	Unit	No.	Test Conditions
Chroma section			,				
Acc control	Cacc (+4)	0	0.7	1.5	dB	14	Input burst 0.2 Vp-p + CW 4.33 MHz shall
characteristics	Cacc (-20)	-6.0	-2.0	0			be 0 dB. Measure the output at pin (12) when the input is changed to +4 dB and -20
							dB, and calculate the ratio of the measured amplitude to the output amplitude at 0 dB.
Killer operation	Ckilr	<b>−54</b>	<b>-</b> 50	<del>-4</del> 2	dB	15	Input a chroma signal of 0.2 Vp-p to the input. Reduce the amplitude and measure the amplitude ratio when the voltage at pin (15) exceeds 2.5 V.
Color control	Cast (4)	2.0	2.2	4.5	dB	16	Input burst 0.2 Vp-p + CW 4.33 MHz,
characteristics	Cast (3)	1.5	2.0	4.0			change V20 to 2 V, 4 V, 3 V, 1 V and 0.5 V
	Cast (1)	-8.5	-6	-4			to measure each output (100 kHz beat)
	Cast (0, 5)	-17	-13	-10			amplitude at pin (12), and calculate the ratio between the measured amplitude and the output amplitude at V20 = 1 V.
APC pull-in	∆ fapc	+350	+600	_	Hz	17	Input only SYNC, and after adjusting free
range		_	-600	-400			run, input 0.2 Vp-p CW ( $\bigcap_{10.2 \text{ Vp-p}} \bigcap_{10.2 \text{ Vp-p}} \bigcap_{1$
B demodulator sensitivity	DB	0.8	1.2	1.6	Vp-p	18	Input CW 4.33 MHz of 0.2 Vp-p to the input, and measure the output amplitude at pin (12) when V20 = 1 V.
Demodulated	R (R/B)	0.46	0.52	0.60	_	19	Input CW 4.33 MHz of 0.2 Vp-p to the input,
out put voltage ratio	R (G/B)	0.20	0.30	0.40			measure the output amplitude at pins (10), (11) when V20 = 1 V, and calculate the ratio of the measured amplitude to the output amplitude in Test No.18 above.
Killer output voltage H	Vkiller H	2.5	3.2	_	V	21	Measure DC voltage at pin (15) when 0 V and 4 V are applied to pin (18).
Killer output voltage L	Vkiller L	_	0.20	0.40			
HD for chroma delay	Dhd	_	2.0	2.2	μѕ	22	Apply B monochromatic wave 0.4 Vp-p and burst 0.2 Vp-p to the input. Measure the delay time from HD pulse rise to the chroma rise of pin (12) output.
IDENT characteristics	ID	_	_	_	_	23	The IDENT (identification) characteristics should be not higher than the killer level.

## **Input Signal**

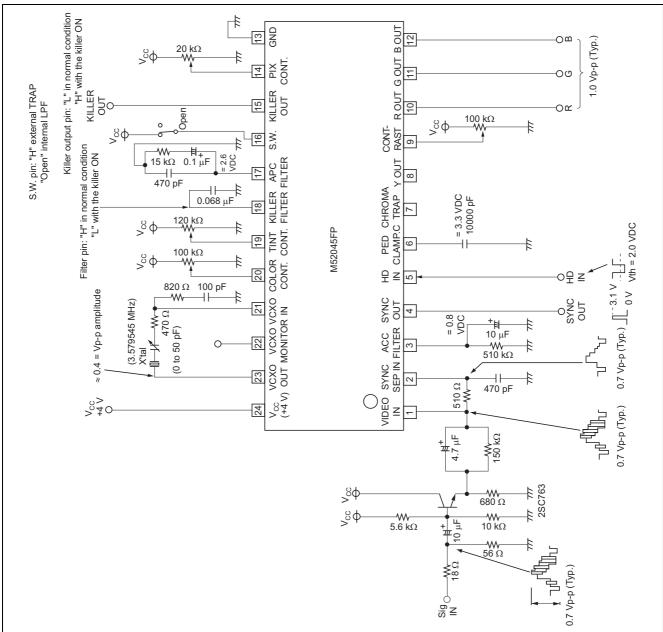


## **Test Circuit**



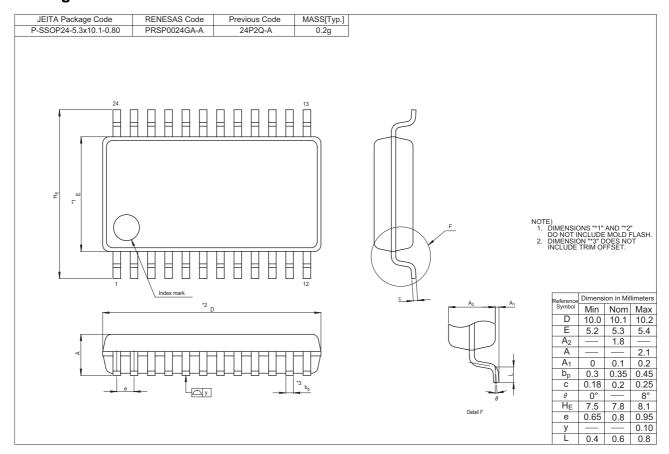
Note: The evaluation of the above application circuit should be performed with great care, because APC characteristics, etc. differ considerable according to crystal characteristics and board pattern.

## **Application Example**



Note: The evaluation of the above application circuit should be performed with great care, because APC characteristics, etc. differ considerably according to crystal characteristics and board pattern.

## **Package Dimensions**



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